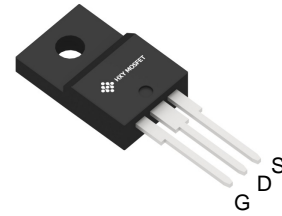


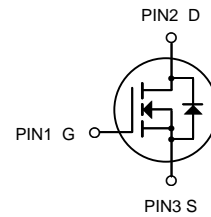


## Description

The R6504KNXC7G can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.



**TO-220F**



N-Channel MOSFET

## General Features

$V_{DS} = 650V, I_D = 10A$   
 $R_{DS(ON)} < 1.05\Omega @ V_{GS} = 10V$

## Application

- Power switch circuit of adaptor and charger.

## Ordering Information

Product ID	Pack	Brand	Units Tube
R6504KNXC7G	TO-220F	HXY MOSFET	50

## Absolute Maximum Ratings@ $T_J = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	650	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Drain Current, V <sub>GS</sub> @ 4.5V	10	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Drain Current, V <sub>GS</sub> @ 4.5V	6.3	A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	40	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	40	W
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>4</sup>	500	mJ
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C



**Electrical Characteristics** (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Unit s
			Min.	Typ.	Max.	
V <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	650	--	--	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Bvdss Temperature Coefficient	ID=250uA,Reference25°C	--	0.7	--	V/°C
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>DS</sub> =650V, V <sub>GS</sub> = 0V, T <sub>a</sub> = 25°C	--	--	1	μA
		V <sub>DS</sub> =520V, V <sub>GS</sub> = 0V, T <sub>a</sub> = 125°C	--	--	100	μA
I <sub>GSS(F)</sub>	Gate to Source Forward Leakage	V <sub>GS</sub> =+30V	--	--	100	nA
I <sub>GSS(R)</sub>	Gate to Source Reverse Leakage	V <sub>GS</sub> =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R <sub>DS(ON)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> =10V,I <sub>D</sub> =5A	--	0.86	1.05	Ω
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0	--	4.0	V
Pulse width tp≤300μs,δ≤2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =15V, I <sub>D</sub> =5A	--	9.5	--	S
C <sub>iSS</sub>	Input Capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz	--	1642	--	pF
C <sub>oss</sub>	Output Capacitance		--	128	--	
C <sub>rSS</sub>	Reverse Transfer Capacitance		--	7	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t <sub>d(ON)</sub>	Turn-on Delay Time	I <sub>D</sub> =10A V <sub>DD</sub> = 325V R <sub>G</sub> =10Ω	--	27	--	ns
t <sub>r</sub>	Rise Time		--	22	--	
t <sub>d(OFF)</sub>	Turn-Off Delay Time		--	53	--	
t <sub>f</sub>	Fall Time		--	24	--	
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =10A V <sub>DD</sub> =520V V <sub>GS</sub> = 10V	--	32	--	nC
Q <sub>gs</sub>	Gate to Source Charge		--	8	--	
Q <sub>gd</sub>	Gate to Drain ("Miller")Charge		--	12	--	



Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$I_S$	Continuous Source Current (Body Diode)		--	--	10	A
$I_{SM}$	Maximum Pulsed Current (Body Diode)		--	--	40	A
$V_{SD}$	Diode Forward Voltage	$I_S=10A, V_{GS}=0V$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$I_S=10A, T_J = 25^\circ C$ $di_F/dt=100A/us,$ $V_{GS}=0V$	--	528	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	3220	--	nC
$I_{RRM}$	Reverse Recovery Current		--	12.2	--	A
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	3.13	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

<sup>a1</sup>: Repetitive rating; pulse width limited by maximum junction temperature <sup>a2</sup>:  $L=10mH, I_D=10A, Start T_J=25^\circ C$

<sup>a3</sup>:  $I_{SD} = 10A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, Start T_J=25^\circ C$



### Characteristics Curve

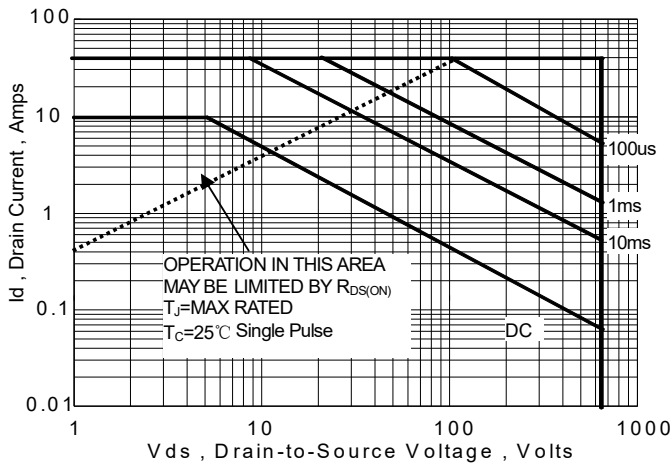


Figure 1 Maximum Forward Bias Safe Operating Area

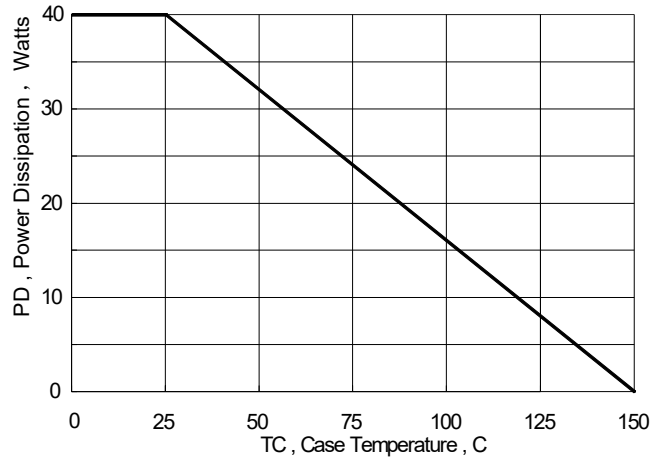


Figure 2 Maximum Power Dissipation vs Case Temperature

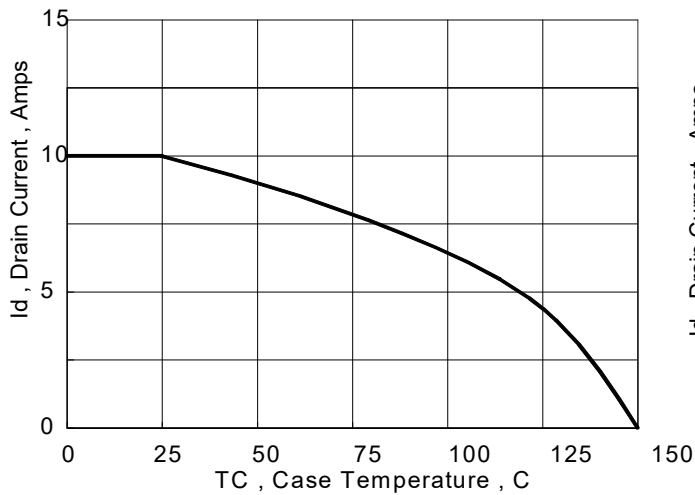


Figure 3 Maximum Continuous Drain Current vs Case Temperature

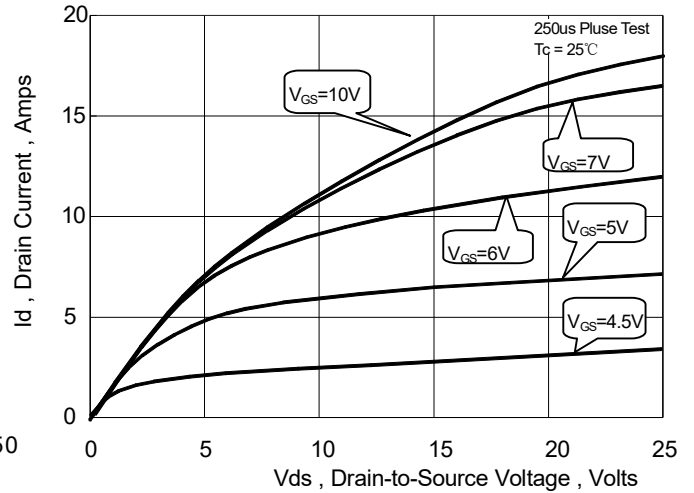


Figure 4 Typical Output Characteristics

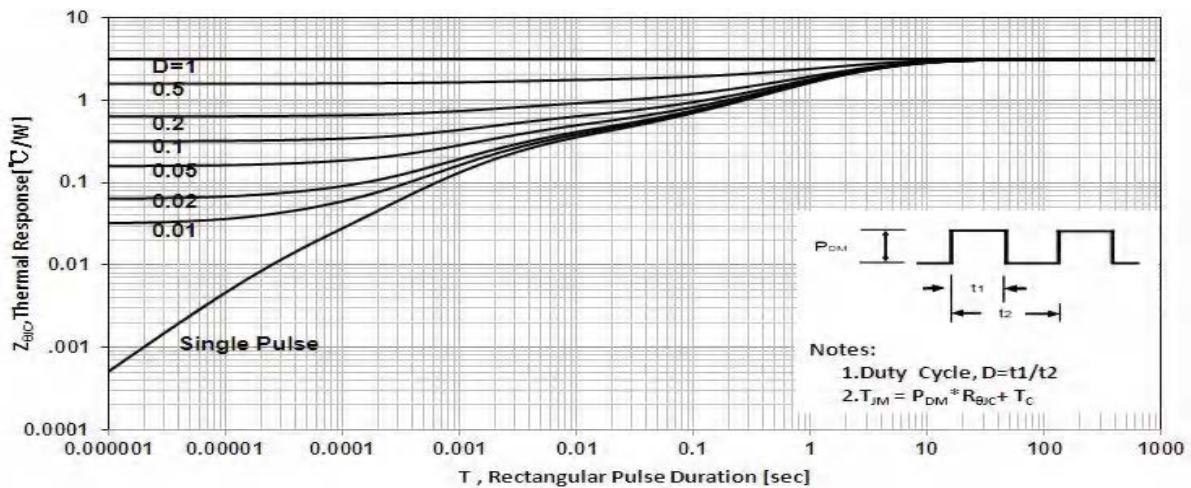


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

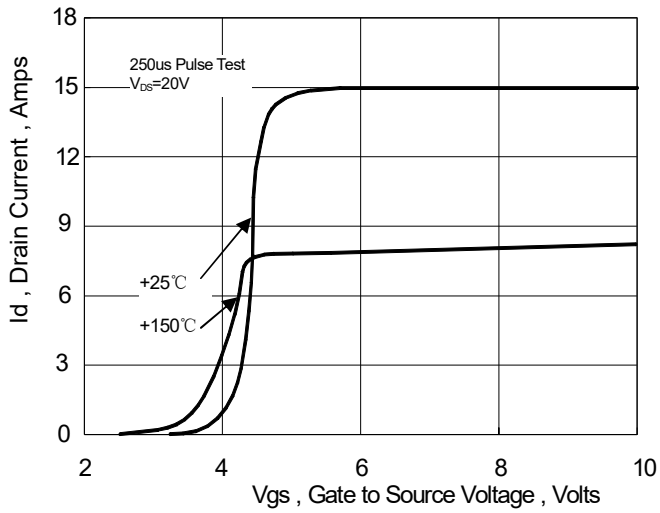


Figure 6 Typical Transfer Characteristics

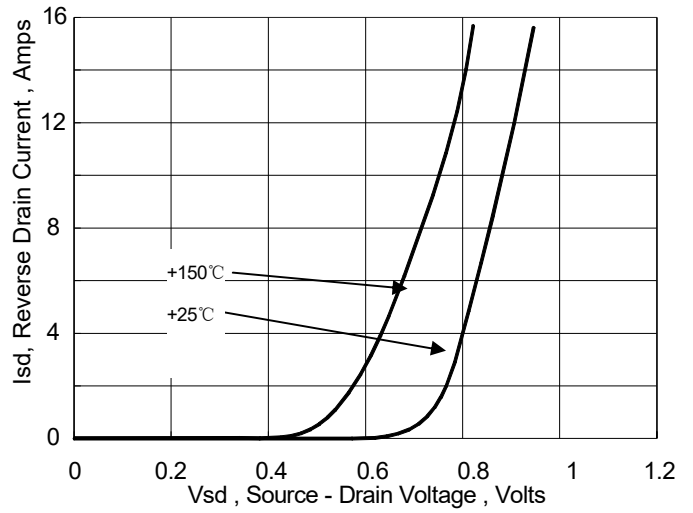


Figure 7 Typical Body Diode Transfer Characteristics

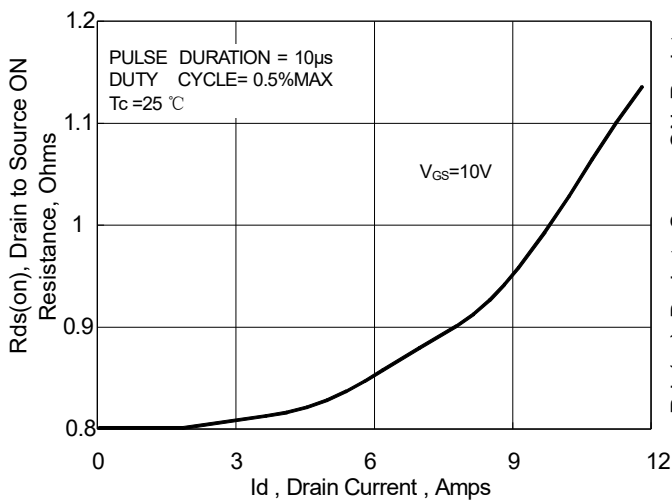


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

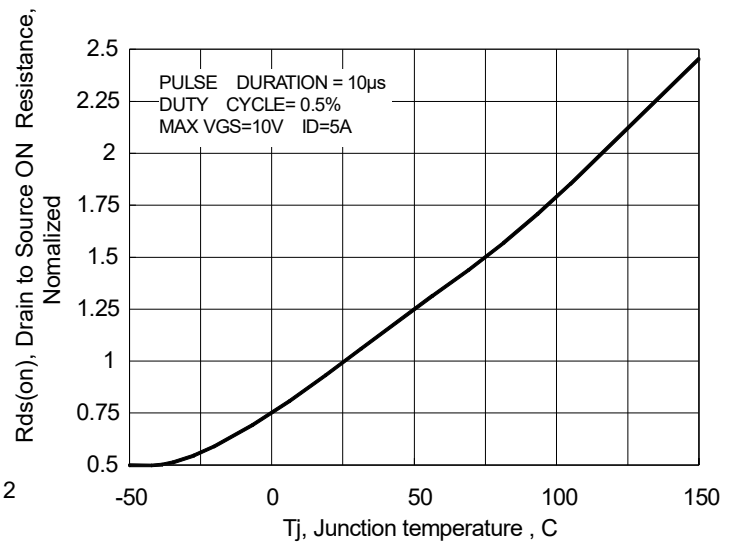


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

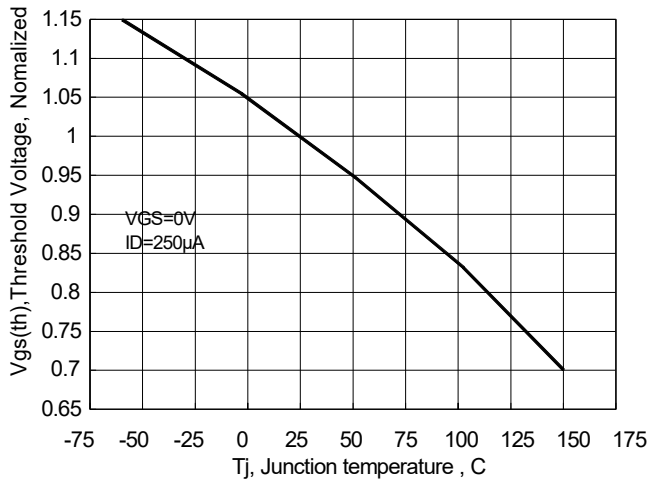


Figure 10 Typical Theshold Voltage vs Junction Temperatur

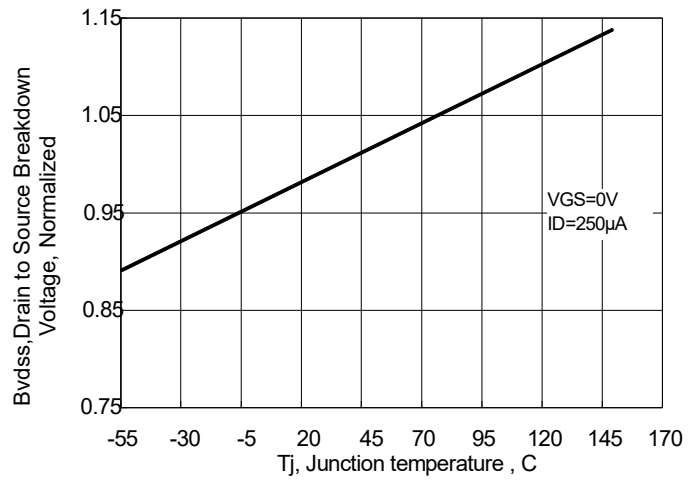


Figure 11 Typical Breakdown Voltage vs Junction Temperature

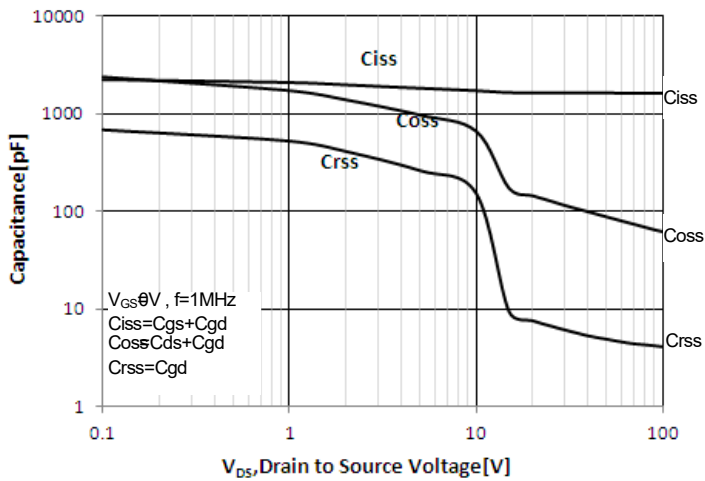


Figure 12 Typical Capacitance vs Drain to Source Voltage

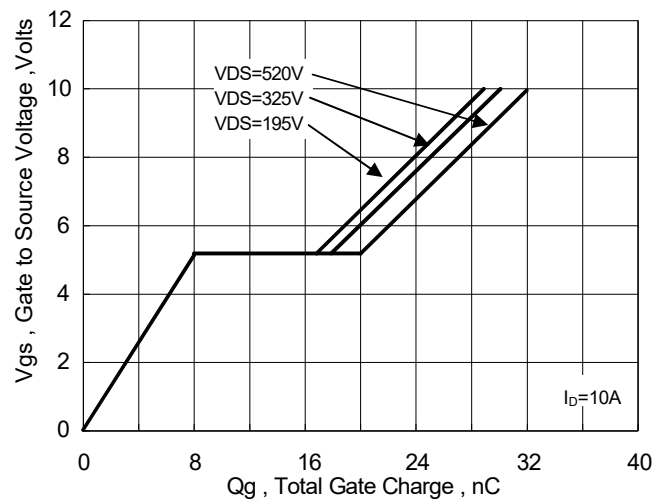


Figure 13 Typical Gate Charge vs Gate to Source Voltage



### Test Circuit and Waveform

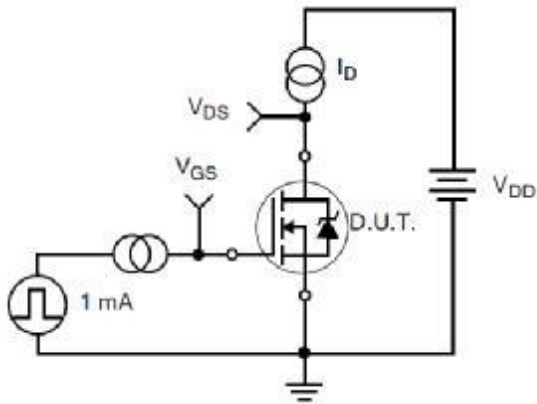


Figure 17. Gate Charge Test Circuit

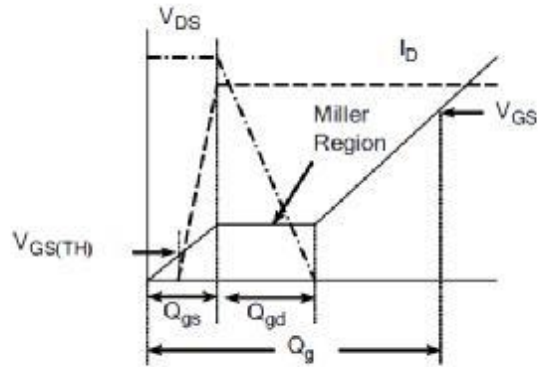


Figure 18. Gate Charge Waveform

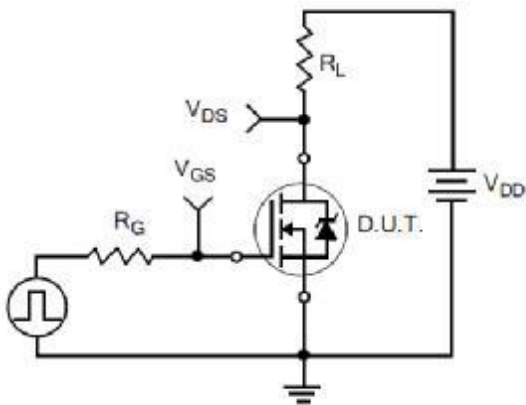


Figure 19. Resistive Switching Test Circuit

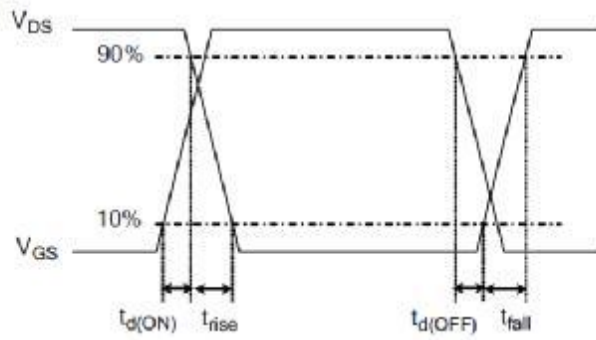


Figure 20. Resistive Switching Waveforms

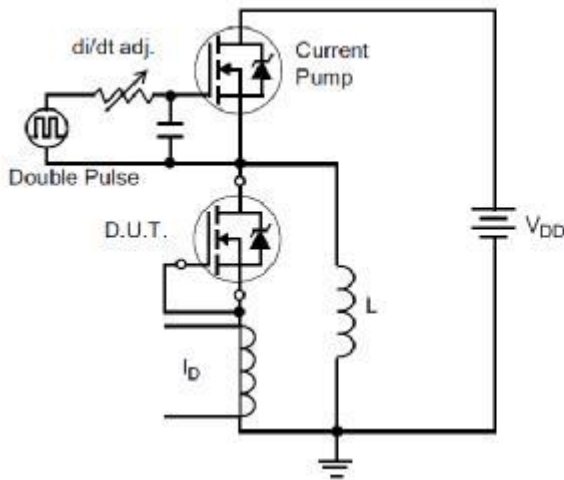


Figure 21. Diode Reverse Recovery Test Circuit

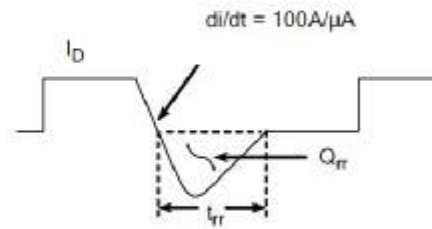


Figure 22. Diode Reverse Recovery Waveform

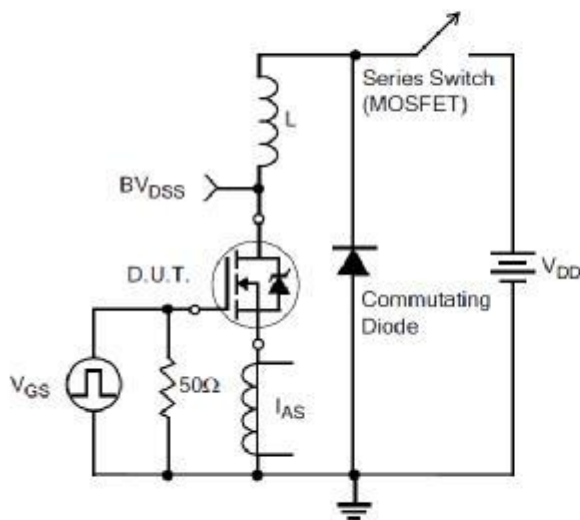


Figure 23. Unclamped Inductive Switching Test Circuit

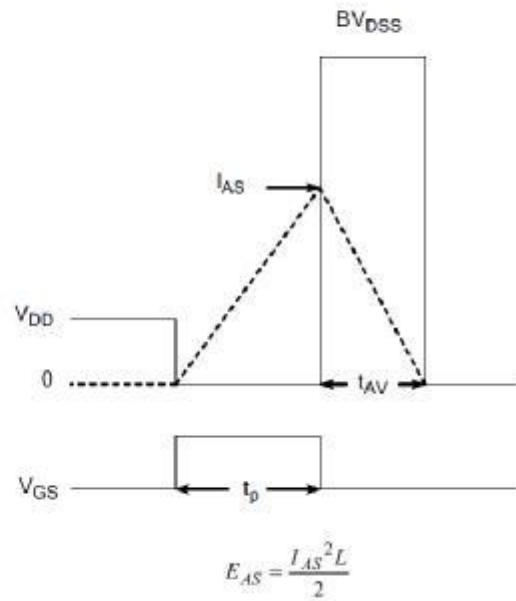
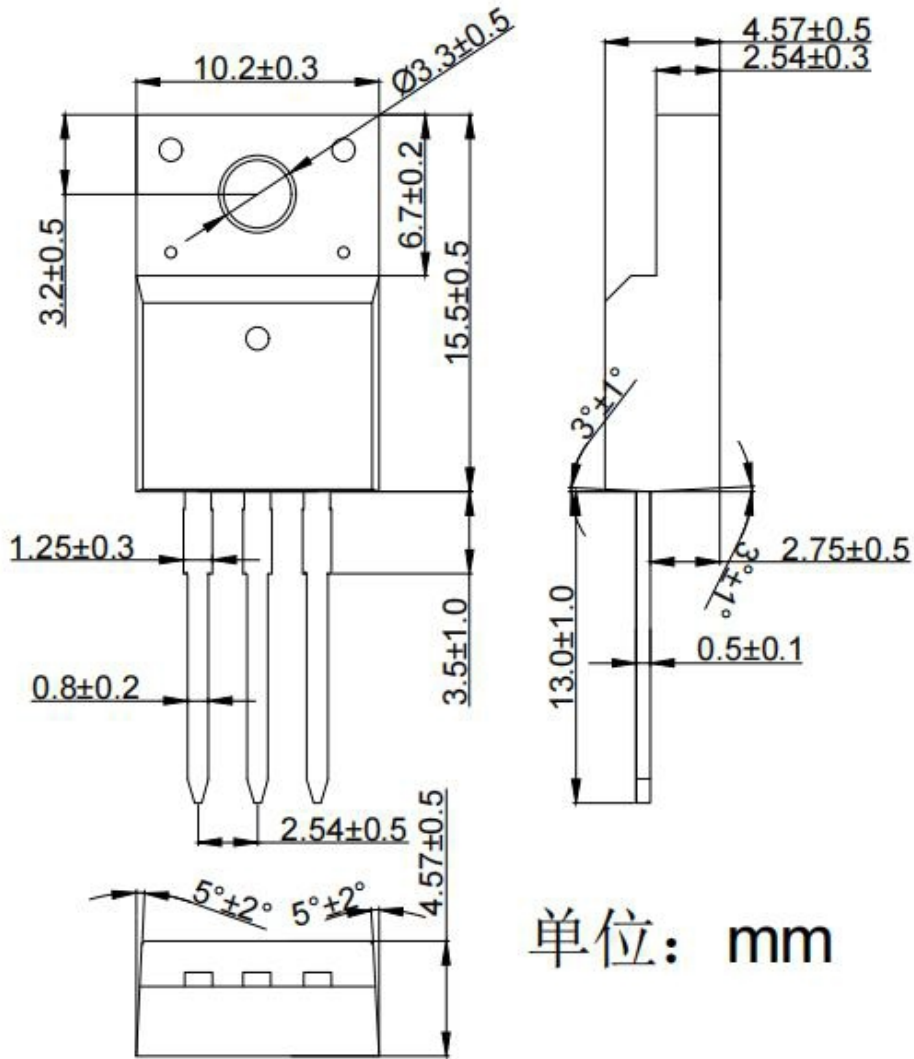


Figure 24. Unclamped Inductive Switching Waveforms



### Package Information

#### TO-220F



单位: mm



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